

PMBFJ174; PMBFJ175; PMBFJ176; PMBFJ177 P-channel silicon field-effect transistors Rev. 3.0 – 24 January 2020

Product data sheet

Product profile 1

1.1 General description

Silicon symmetrical p-channel junction FETs in plastic microminiature SOT23 envelopes. They are intended for application with analogue switches, choppers, commutators etc. using SMD technology. A special feature is the interchangeability of the drain and source connections.

1.2 Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{DS}	drain-source voltage		30	-	30	V
V _{GSo}	gate-source voltage		-	-	30	V
-I _G	gate current		-	-	50	mA
P _{tot}	total power dissipation	up to T _{amb} = 25 ° C	-	-	300	mW
-I _{DSS}	drain current	-V _{DS} = 15 V; V _{GS} = 0				
		PMBFJ174	20	-	135	mA
		PMBFJ175	7	-	70	mA
		PMBFJ176	2	-	35	mA
		PMBFJ177	1.5	-	20	mA
R _{DS on}	drain-source ON-	-V _{DS} = 0.1 V; V _{GS} = 0				
	resistance	PMBFJ174	-	-	85	Ω
		PMBFJ175	-	-	125	Ω
		PMBFJ176	-	-	250	Ω
		PMBFJ177	-	-	300	Ω

Table 1. Quick reference data



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2 Pinning information

Pin	Description ^[1]	Simplified outline	Symbol
1	drain		
2	source		$3 \rightarrow 2$
3	gate		sym053

[1] Drain and source are interchangeable.

3 Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
PMBFJ174	-	plastic surface mounted package; 3 leads	SOT23			
PMBFJ175						
PMBFJ176	-					
PMBFJ177						

4 Marking

Table 4. Marking	
Type number	Marking code ^[1]
PMBFJ174	*6X
PMBFJ175	*6W
PMBFJ176	*6S
PMBFJ177	*6Y

[1] * = manufacturing site

5 Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage		30	30	V
V _{GSO}	gate-source voltage		-	30	V
V _{GDO}	gate-drain voltage		-	30	V

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Symbol	Parameter	Conditions		Min	Max	Unit
-I _G	gate current (DC)			-	50	mA
P _{tot}	total power dissipation	T _{amb} = 25 ° C	[1]	-	300	mW
T _{stg}	storage temperature range			-65	150	°C
Tj	junction temperature			-	150	° C

[1] Mounted on a ceramic substrate, 8 mm × 10 mm × 0.7 mm.

6 Thermal characteristics

Table 6. Thermal characteristics

 $T_j = P \left(R_{th(j-t)} + R_{th(t-s)} + R_{th(s-a)} \right) + T_{amb}.$

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-a)}	junction to ambient in free air thermal resistance		430	K/W

7 Static characteristics

Table 7. Static characteristics

 $T_i = 25 \circ C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
I _{GSS}	gate cut-off current							
	PMBFJ174	V_{GS} = 20 V; V_{DS} = 0 V	-	-	1	nA		
	PMBFJ175	V _{GS} = 20 V; V _{DS} = 0 V	-	-	1	nA		
	PMBFJ176	V_{GS} = 20 V; V_{DS} = 0 V	-	-	1	nA		
	PMBFJ177	V_{GS} = 20 V; V_{DS} = 0 V	-	-	1	nA		
I _{DSX}	drain cut-off current							
	PMBFJ174	-V _{DS} = 15 V; V _{GS} = 10 V	-	-	1	nA		
	PMBFJ175	-V _{DS} = 15 V; V _{GS} = 10 V	-	-	1	nA		
	PMBFJ176	-V _{DS} = 15 V; V _{GS} = 10 V	-	-	1	nA		
	PMBFJ177	-V _{DS} = 15 V; V _{GS} = 10 V	-	-	1	nA		
I _{DSS}	drain current							
	PMBFJ174	V_{DS} = -15 V; V_{GS} = 0 V	20	-	135	mA		
	PMBFJ175	-V _{DS} = 15 V; V _{GS} = 0 V	7	-	70	mA		
	PMBFJ176	-V _{DS} = 15 V; V _{GS} = 0 V	2	-	35	mA		
	PMBFJ177	-V _{DS} = 15 V; V _{GS} = 0 V	1.5	-	20	mA		
√ _{(BR)GSS}	gate-source breakdown voltage							
	PMBFJ174	I_{G} = 1 µA; V_{DS} = 0 V	-	-	30	V		
	PMBFJ175	I_{G} = 1 µA; V_{DS} = 0 V	-	-	30	V		
	PMBFJ176	I _G = 1 μΑ; V _{DS} = 0 V	-	-	30	V		
	PMBFJ177	I _G = 1 μA; V _{DS} = 0 V	-	-	30	V		

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
V _{GSoff}	gate-source cut-off voltage							
	PMBFJ174	-I _D = 10 nA; V _{DS} = -15 V	5	-	10	V		
	PMBFJ175	-I _D = 10 nA; V _{DS} = -15 V	3	-	6	V		
	PMBFJ176	-I _D = 10 nA; V _{DS} = -15 V	1	-	4	V		
	PMBFJ177	-I _D = 10 nA; V _{DS} = -15 V	0.8	-	2.25	V		
R _{DSon}	drain-source on resistance							
	PMBFJ174	-V _{DS} = 0.1 V; V _{GS} = 0 V	-	-	85	Ω		
	PMBFJ175	-V _{DS} = 0.1 V; V _{GS} = 0 V	-	-	125	Ω		
	PMBFJ176	-V _{DS} = 0.1 V; V _{GS} = 0 V	-	-	250	Ω		
	PMBFJ177	-V _{DS} = 0.1 V; V _{GS} = 0 V	-	-	300	Ω		

8 Dynamic characteristics

Table 8. Dynamic characteristics

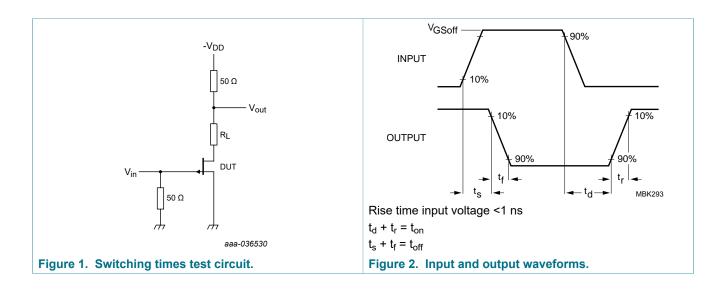
 $T_i = 25 \circ C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{iss}	input capacitance	V_{GS} = 10 V; V_{DS} = 0 V; f = 1 MHz	-	8	-	pF
		V _{DS} = 0 V; V _{GS} = 0 V; f = 1 MHz	-	30	-	pF
C _{rs}	feedback capacitance	V _{GS} = 10 V; V _{DS} = 0 V; f = 1 MHz	-	4	-	pF
Switching	j times; see <u>Figure 1</u>and	Figure 2, Test conditions for switching times are	e as follows: ^[1]		1	
d	delay time					
	PMBFJ174		-	2	-	ns
	PMBFJ175		-	5	-	ns
	PMBFJ176		-	15	-	ns
	PMBFJ177		-	20	-	ns
r	rise time					
	PMBFJ174		-	5	-	ns
	PMBFJ175		-	10	-	ns
	PMBFJ176		-	20	-	ns
	PMBFJ177		-	25	-	ns
on	turn-on time					
	PMBFJ174		-	7	-	ns
	PMBFJ175		-	15	-	ns
	PMBFJ176		-	35	-	ns
	PMBFJ177		-	45	-	ns

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
t _s	storage temperature					
	PMBFJ174		-	5	-	ns
	PMBFJ175		-	10	-	ns
	PMBFJ176		-	15	-	ns
	PMBFJ177		-	20	-	ns
t _f	fall time					
	PMBFJ174		-	10	-	ns
	PMBFJ175		-	20	-	ns
	PMBFJ176		-	20	-	ns
	PMBFJ177		-	25	-	ns
t _{off}	turn-off time					
	PMBFJ174		-	6	-	ns
	PMBFJ175		-	6	-	ns
	PMBFJ176		-	6	-	ns
	PMBFJ177		-	6	-	ns



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9 Package outline

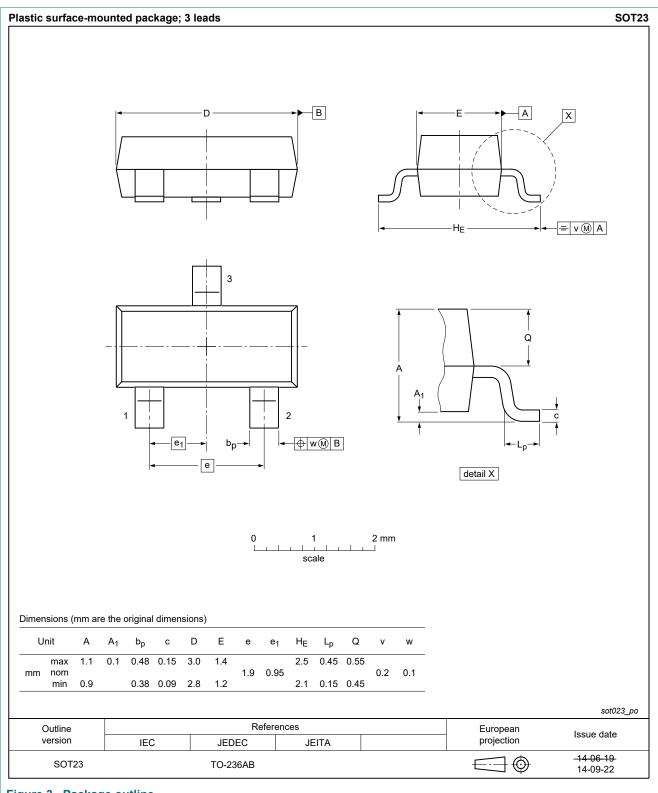


Figure 3. Package outline.

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10 Revision history

Revision hist	Revision history					
Revision number	Date	Description				
3.0	20200124	Product data sheet				
modification	 adapted the n 	otation of the manufacturing code				
2.0	19950401	product data sheet				
1.0		Initial version of the document				

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11 Legal information

11.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition	
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.	
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.	
Product [short] data sheet	Production	This document contains the product specification.	

Please consult the most recently issued document before initiating or completing a design. [1]

[2] [3] The term 'short data sheet' is explained in section "Definitions".

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